

# **Bipolar Transistor**

50 V, 15 A, Low V<sub>CE(sat)</sub>, NPN TO-220F-3SG

## 2SC6082

#### **Features**

- Adoption of MBIT Process
- Low Collector-to-Emitter Saturation Voltage
- Large Current Capacitance
- High-Speed Switching
- This is a Pb-Free Device

## **Applications**

 High-Speed Switching Applications (Switching Regulator, Driver Circuit)

## **Specifications**

## **ABSOLUTE MAXIMUM RATINGS** (Ta = 25°C)

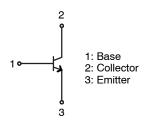
| Symbol           | Rating                       | Condition                     | Value          | Unit |
|------------------|------------------------------|-------------------------------|----------------|------|
| V <sub>CBO</sub> | Collector-to-Base Voltage    |                               | 60             | V    |
| V <sub>CES</sub> | Collector-to-Emitter Voltage |                               | 60             | V    |
| V <sub>CEO</sub> |                              |                               | 50             | V    |
| V <sub>EBO</sub> | Emitter-to-Base Voltage      |                               | 6              | V    |
| I <sub>C</sub>   | Collector Current            |                               | 15             | Α    |
| I <sub>CP</sub>  | Collector Current (Pulse)    | PW ≤ 10 μs,<br>duty cycle ≤1% | 20             | Α    |
| I <sub>B</sub>   | Base Current                 |                               | 3              | Α    |
| P <sub>C</sub>   | Collector Dissipation        |                               | 2              | W    |
|                  |                              | T <sub>C</sub> = 25°C         | 23             | W    |
| Tj               | Junction Temperature         |                               | 150            | °C   |
| Tstg             | Storage Temperature          |                               | –55 to<br>+150 | °C   |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

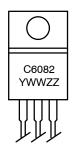


TO-220 Fullpack, 3-Lead / TO-220F-3SG CASE 221AT

#### **ELECTRICAL CONNECTION**



#### **MARKING DIAGRAM**



C6082

= Device Code

YWW ZZ = Date Code (Year & Week)

= Assembly Lot

#### **ORDERING INFORMATION**

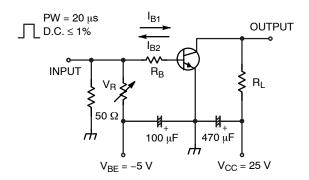
| Device     | Package              | Shipping  |
|------------|----------------------|-----------|
| 2SC6082-1E | TO-220F<br>(Pb-Free) | 50 / Tube |

## **ELECTRICAL CHARACTERISTICS** (Ta = 25°C)

| Symbol                | Parameter                               | Conditions                                       | Min | Тур | Max | Unit |
|-----------------------|---|--|-----|-----|-----|------|
| I <sub>CBO</sub>      | Collector Cutoff Current                | V <sub>CB</sub> = 40 V, I <sub>E</sub> = 0 A     | -   | -   | 10  | μΑ   |
| I <sub>EBO</sub>      | Emitter Cutoff Current                  | $V_{EB} = 4 \text{ V}, I_{C} = 0 \text{ A}$      | -   | -   | 10  | μΑ   |
| H <sub>FE</sub> 1     | DC Current Gain                         | $V_{CE} = 2 \text{ V, } I_{C} = 330 \text{ mA}$  | 200 | -   | 560 |      |
| H <sub>FE</sub> 2     |   | V <sub>CE</sub> = 2 V, I <sub>C</sub> = 10 A     | 50  | -   | -   |      |
| f <sub>T</sub>        | Gain-Bandwidth Product                  | V <sub>CE</sub> = 10 V, I <sub>C</sub> = 2 A     | -   | 195 | -   | MHz  |
| Cob                   | Output Capacitance                      | V <sub>CB</sub> = 10 V, f = 1 MHz                | -   | 85  | -   | pF   |
| V <sub>CE</sub> (sat) | Collector-to-Emitter Saturation Voltage | I <sub>C</sub> = 7.5 mA, I <sub>B</sub> = 375 mA | -   | 200 | 400 | mV   |
| V <sub>BE</sub> (sat) | Base-to-Emitter Saturation Voltage      | $I_C = 7.5 \text{ mA}, I_B = 375 \text{ mA}$     | -   | -   | 1.2 | V    |
| V <sub>(BR)CBO</sub>  | Collector-to-Base Breakdown Voltage     | $I_C = 100 \mu A, I_E = 0 A$                     | 60  | -   | -   | V    |
| V <sub>(BR)CES</sub>  | Collector-to-Emitter Breakdown Voltage  | $I_C$ = 100 μA, $R_{BE}$ = 0 $\Omega$            | 60  | -   | -   | V    |
| V <sub>(BR)CEO</sub>  |   | $I_C = 1$ mA, $R_{BE} = \infty$                  | 50  | -   | -   | V    |
| V <sub>(BR)EBO</sub>  | Emitter-to-Base Breakdown Voltage       | I <sub>E</sub> = 100 μA, I <sub>C</sub> = 0 A    | 5   | -   | -   | V    |
| t <sub>on</sub>       | Turn-On Time                            | See specified Test Circuit                       |     | 52  | -   | ns   |
| t <sub>stg</sub>      | Storage Time                            | 1  |     | 560 | -   | ns   |
| t <sub>f</sub>        | Fall Time                               |  |     | 37  | -   | ns   |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

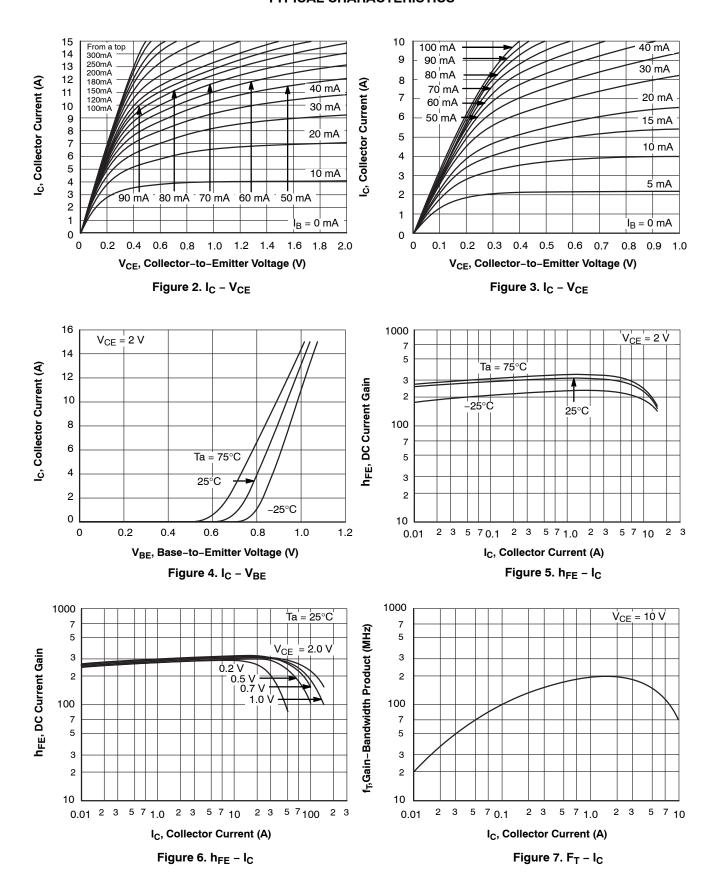
## **Switching Time Test Circuit**



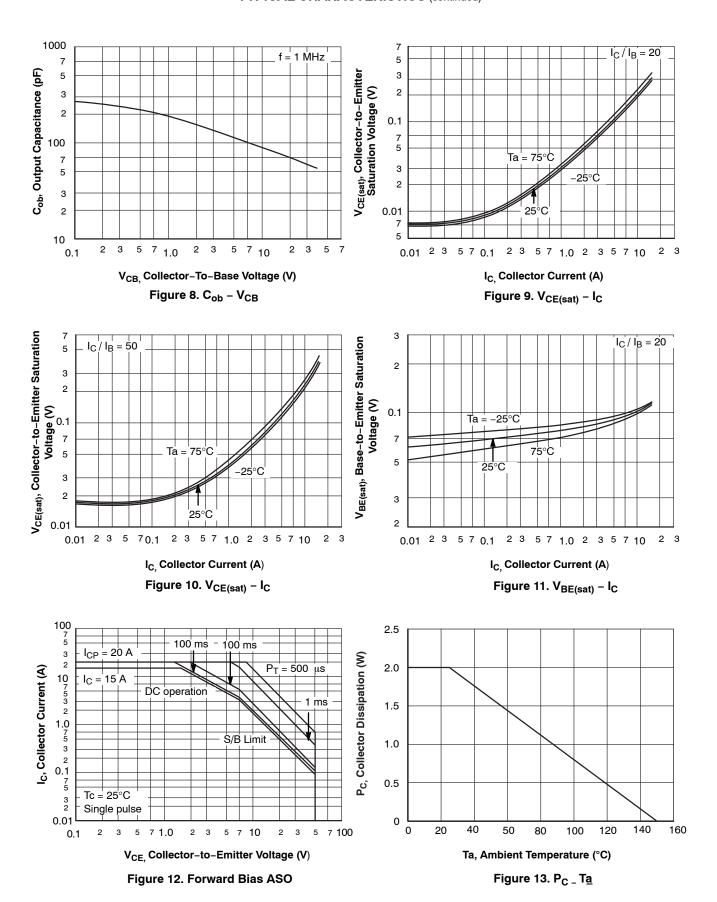
 $I_C = 20I_{B1} = -20I_{B2} = 5 \text{ A}$ 

Figure 1. Switching Time Test Circuit

## **TYPICAL CHARACTERISTICS**



## TYPICAL CHARACTERISTICS (continued)



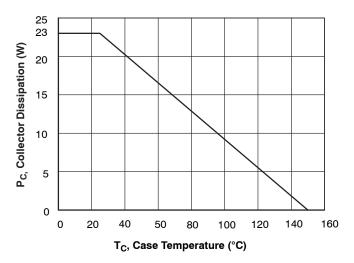
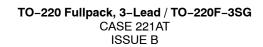
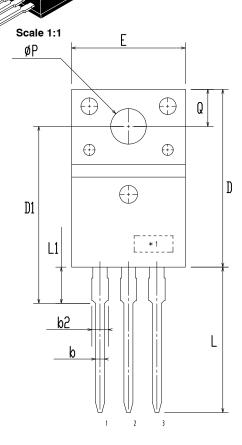


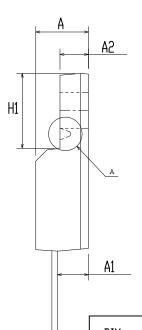
Figure 14. P<sub>C</sub> – T<sub>C</sub>

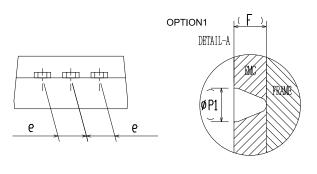




**DATE 19 JAN 2021** 







| DIM   | HILLIHITEKS |       |       |  |
|-------|-------------|-------|-------|--|
| ויונע | MIN         | NDM   | MAX   |  |
| Α     | 4.50        | 4.70  | 4.90  |  |
| A1    | 2.56        | 2.76  | 2.96  |  |
| A2    | 2.34        | 2.54  | 2.74  |  |
| b     | 0.70        | 0.80  | 0.90  |  |
| b2    | ~           | 2     | 1.47  |  |
| С     | 0.45        | 0.50  | 0.60  |  |
| D     | 15.67       | 15.87 | 16.07 |  |
| D1    | 15.60       | 15.80 | 16.00 |  |
| E     | 9.96        | 10.16 | 10.36 |  |
| е     | 2.34        | 2.54  | 2.74  |  |
| F     | ~           | 0.84  | ~     |  |
| H1    | 6.48        | 6.68  | 6.88  |  |
| L     | 12.78       | 12.98 | 13.18 |  |
| L1    | 3.03        | 3.23  | 3.43  |  |
| øΡ    | 2.98        | 3.18  | 3.38  |  |
| ø P1  | ~           | 1.00  | ~     |  |
| Q     | 3.20        | 3.30  | 3.40  |  |
|       |             |       |       |  |

MILL IMITERS

## NOTES:

- A. DIMENSION AND TOLERANCE AS ASME Y14.5-2009
- B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUCSIONS.

C

C. OPTION 1 - WITH SUPPORT PIN HOLE OPTION 2 - NO SUPPORT PIN HOLE

| DOCUMENT NUMBER: | 98AON67439E                             | Electronic versions are uncontrolled except when accessed directly from the Document Repository.<br>Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. |             |  |
|------------------|---|---|-------------|--|
| DESCRIPTION:     | : TO-220 FULLPACK, 3-LEAD / TO-220F-3SG |   | PAGE 1 OF 1 |  |

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

#### ADDITIONAL INFORMATION

**TECHNICAL PUBLICATIONS:** 

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$ 

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales